

| SOP-8 | F |
|-------|---|
|       | 1 |
| -1 -  | 2 |
|       | 4 |
| 8 1   |   |

### Pin Definition:

| 8. Drain 1 |
|------------|
| 7. Drain 1 |
| 6. Drain 2 |
| 5. Drain 2 |
|            |

### PRODUCT SUMMARY

G1 C

| V <sub>DS</sub> (V) | V <sub>DS</sub> (V) R <sub>DS(on)</sub> (mΩ) |     |
|---------------------|--|-----|
| 60                  | 55 @ V <sub>GS</sub> = 10V                   | 4.5 |
|                     | 75 @ V <sub>GS</sub> = 4.5V                  | 3.9 |

**Block Diagram** 

G<sub>2</sub> C

**Dual N-Channel MOSFET** 

D<sub>2</sub>

S<sub>2</sub>

D<sub>1</sub>

S-

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

#### **Application**

- High-Side DC/DC Conversion
- Notebook
- Sever

#### **Ordering Information**

| Part No.       | Package | Packing            |
|----------------|---------|--------------------|
| TSM4946DCS RL  | SOP-8   | 2.5Kpcs / 13" Reel |
| TSM4946DCS RLG | SOP-8   | 2.5Kpcs / 13" Reel |

Note: "G" denote for Green Product

#### Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

| Parameter   | Symbol    | Limit                             | Unit         |     |  |
|---|-----------|-----------------------------------|--------------|-----|--|
| Drain-Source Voltage  |           | V <sub>DS</sub>                   | 60           | V   |  |
| Gate-Source Voltage   |           | $V_{GS}$                          | ±20          | V   |  |
| Continuous Drain Current                                    |           | I <sub>D</sub>                    | 4.5          | А   |  |
| Pulsed Drain Current  |           | I <sub>DM</sub>                   | 30           | А   |  |
| Continuous Source Current (Diode Conduction) <sup>a,b</sup> |           | I <sub>S</sub>                    | 2            | А   |  |
|   | Ta = 25°C |                                   | 2.4          | 14/ |  |
| Maximum Power Dissipation                                   | Ta = 75°C | – P <sub>D</sub>                  | 1.7          | W   |  |
| Operating Junction Temperature                              |           | TJ                                | +150         | °C  |  |
| Operating Junction and Storage Temperature Range            |           | T <sub>J</sub> , T <sub>STG</sub> | - 55 to +150 | °C  |  |

#### **Thermal Performance**

| Parameter  | Symbol           | Limit | Unit |
|--|------------------|-------|------|
| Junction to Case Thermal Resistance                  | RƏ <sub>JF</sub> | 32    | °C/W |
| Junction to Ambient Thermal Resistance (PCB mounted) | RƏ <sub>JA</sub> | 62.5  | °C/W |

Notes:

a. Pulse width limited by the Maximum junction temperature

b. Surface Mounted on FR4 Board, t  $\leq$  10 sec.



### **Electrical Specifications**

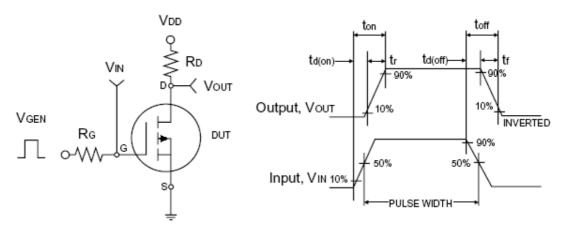
| Parameter                                     | Conditions                                 | Symbol              | Min | Тур | Max  | Unit  |
|---|--|---------------------|-----|-----|------|-------|
| Static  |  |                     |     |     | •    |       |
| Drain-Source Breakdown Voltage                | $V_{GS} = 0V, I_{D} = 250uA$               | $BV_{DSS}$          | 60  |     |      | V     |
| Gate Threshold Voltage                        | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$       | V <sub>GS(TH)</sub> | 1   |     | 3    | V     |
| Gate Body Leakage                             | $V_{GS} = \pm 20V, V_{DS} = 0V$            | I <sub>GSS</sub>    |     |     | ±100 | nA    |
| Zero Gate Voltage Drain Current               | $V_{DS} = 60V, V_{GS} = 0V$                | I <sub>DSS</sub>    |     |     | 2    | μA    |
| On-State Drain Current <sup>a</sup>           | $V_{DS} = 5V, V_{GS} = 10V$                | I <sub>D(ON)</sub>  | 20  |     |      | А     |
| Drain-Source On-State Resistance <sup>a</sup> | $V_{GS} = 10V, I_{D} = 4.5A$               | Б                   |     | 45  | 55   | mΩ    |
| Drain-Source On-State Resistance              | $V_{GS} = 4.5V, I_{D} = 3.9A$              | R <sub>DS(ON)</sub> |     | 55  | 75   |       |
| Forward Transconductance <sup>a</sup>         | $V_{DS} = 15V, I_{D} = 4.5A$               | g <sub>fs</sub>     |     | 13  |      | S     |
| Diode Forward Voltage                         | $I_{S} = 2A, V_{GS} = 0V$                  | V <sub>SD</sub>     |     | 0.9 | 1.2  | V     |
| Dynamic <sup>b</sup>                          |  |                     |     |     |      |       |
| Total Gate Charge                             |  | Q <sub>g</sub>      |     | 19  | 30   |       |
| Gate-Source Charge                            | $V_{DS} = 30V, I_D = 4.5A,$                | $Q_{gs}$            |     | 4   |      | nC    |
| Gate-Drain Charge                             | V <sub>GS</sub> = 10V                      | $Q_gd$              |     | 3   |      |       |
| Input Capacitance                             |  | C <sub>iss</sub>    |     | 910 |      |       |
| Output Capacitance                            | $V_{DS} = 24V, V_{GS} = 0V,$<br>f = 1.0MHz | C <sub>oss</sub>    |     | 145 |      | pF    |
| Reverse Transfer Capacitance                  |  | C <sub>rss</sub>    |     | 67  |      |       |
| Switching <sup>c</sup>                        |  |                     |     |     |      |       |
| Turn-On Delay Time                            |  | t <sub>d(on)</sub>  |     | 13  | 20   |       |
| Turn-On Rise Time                             | $V_{DD} = 30V, R_L = 30\Omega,$            | t <sub>r</sub>      |     | 11  | 20   | ~ ~ ~ |
| Turn-Off Delay Time                           | $I_D = 1A, V_{GEN} = 10V,$                 | t <sub>d(off)</sub> |     | 36  | 60   | nS    |
| Turn-Off Fall Time                            | $R_{G} = 6\Omega$                          | t <sub>f</sub>      |     | 11  | 20   |       |

#### Notes:

a. pulse test: PW ≤300µS, duty cycle ≤2%

b. For DESIGN AID ONLY, not subject to production testing.

b. Switching time is essentially independent of operating temperature.

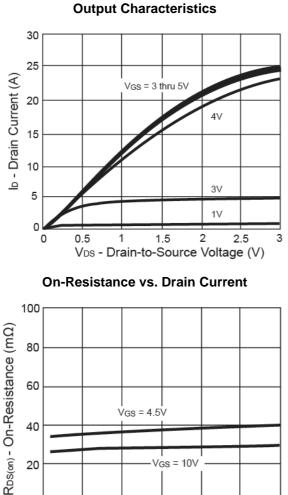


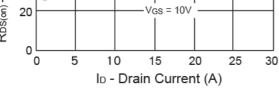
Switching Test Circuit

Switchin Waveforms

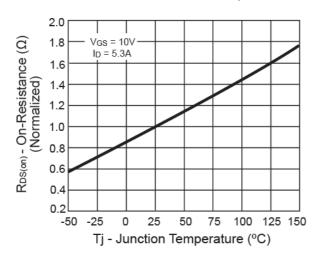


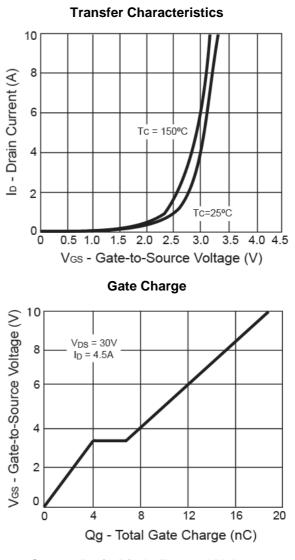
#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



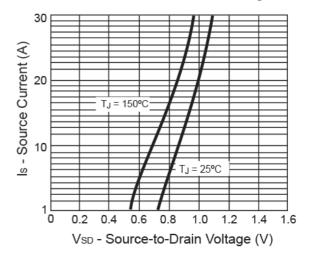


**On-Resistance vs. Junction Temperature** 



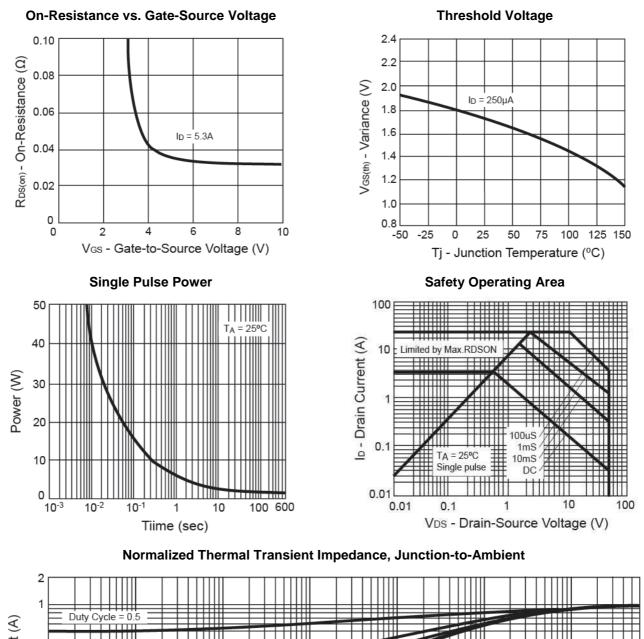


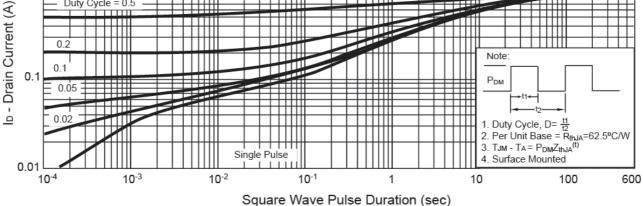
Source-Drain Diode Forward Voltage





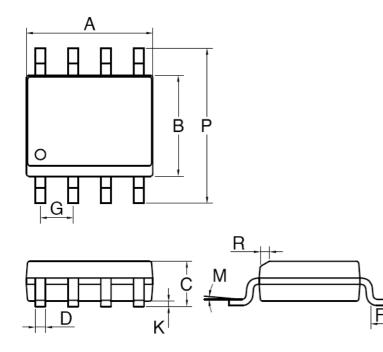
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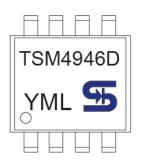


### **SOP-8 Mechanical Drawing**



| SOP-8 DIMENSION |             |      |           |       |  |  |
|-----------------|-------------|------|-----------|-------|--|--|
| DIM             | MILLIMETERS |      | INCHES    |       |  |  |
|                 | MIN         | MAX  | MIN       | MAX.  |  |  |
| Α               | 4.80        | 5.00 | 0.189     | 0.196 |  |  |
| В               | 3.80        | 4.00 | 0.150     | 0.157 |  |  |
| С               | 1.35        | 1.75 | 0.054     | 0.068 |  |  |
| D               | 0.35        | 0.49 | 0.014     | 0.019 |  |  |
| F               | 0.40        | 1.25 | 0.016     | 0.049 |  |  |
| G               | 1.27        | BSC  | C 0.05BS0 |       |  |  |
| K               | 0.10        | 0.25 | 0.004     | 0.009 |  |  |
| М               | 0°          | 7°   | 0°        | 7°    |  |  |
| Р               | 5.80        | 6.20 | 0.229     | 0.244 |  |  |
| R               | 0.25        | 0.50 | 0.010     | 0.019 |  |  |

### **Marking Diagram**



- Y = Year Code
- M = Month Code
  - (A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)
  - = Month Code for Halogen Free Product
  - (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
- L = Lot Code



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